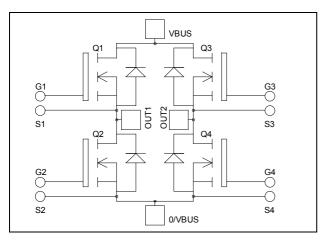
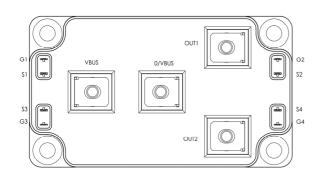


Full - Bridge MOSFET Power Module

$V_{DSS} = 1000V$ $R_{DSon} = 180m\Omega \text{ typ } @ \text{ Tj} = 25^{\circ}\text{C}$ $I_D = 43\text{ } @ \text{ Tc} = 25^{\circ}\text{C}$





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage		1000	V
I_D	Continuous Drain Current	$T_c = 25^{\circ}C$	43	
	Continuous Drain Current	$T_c = 80^{\circ}C$	33	А
I _{DM}	Pulsed Drain current	172		
V _{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		210	mΩ
PD	Maximum Power Dissipation	$T_c = 25^{\circ}C$	780	W
I _{AR}	Avalanche current (repetitive and non repetitive)		25	А
EAR	Repetitive Avalanche Energy		50	mJ
E _{AS}	Single Pulse Avalanche Energy		3000	IIIJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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www.microsemi.com

Downloaded from: http://www.datasheetcatalog.com/



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$	$T_j = 25^{\circ}C$			200	A	
		$V_{GS} = 0V, V_{DS} = 800V$	$T_j = 125^{\circ}C$			1000	μA	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 21.5A$			180	210	mΩ	
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$		3		5	V	
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	1			±150	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		10.4		
Coss	Output Capacitance	$V_{\rm DS} = 25 V$		1.76		nF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		0.32		
Qg	Total gate Charge	$V_{GS} = 10V$		372		nC
Q _{gs}	Gate – Source Charge	$V_{Bus} = 500V$		48		
Q_{gd}	Gate – Drain Charge	$I_D = 43A$		244		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 670V$ $I_D = 43A$ $R_G = 2.5\Omega$		18		ns
Tr	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			155		
$T_{\rm f}$	Fall Time			40		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V$, $V_{Bus} = 670V$ $I_D = 43A$, $R_G = 2.5\Omega$		1800		I
E_{off}	Turn-off Switching Energy			1246		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V$, $V_{Bus} = 670V$ $I_D = 43A$, $R_G = 2.5\Omega$		2846		т
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy			1558		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$			43	А
	(Body diode)		$Tc = 80^{\circ}C$			33	Λ
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -43A$				1.3	V
dv/dt	Peak Diode Recovery 1					18	V/ns
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$			320	ns
	Reverse Receivery Time	$I_{\rm S} = -43A$ $V_{\rm R} = 670V$	$T_{j} = 125^{\circ}C$			650	115
Q _{rr}	Reverse Recovery Charge	$di_{\rm S}/dt = 200 {\rm A}/\mu{\rm s}$	$T_j = 25^{\circ}C$		7.2		μC
	Reverse Receivery Charge		$T_{j} = 125^{\circ}C$		19.5		μυ

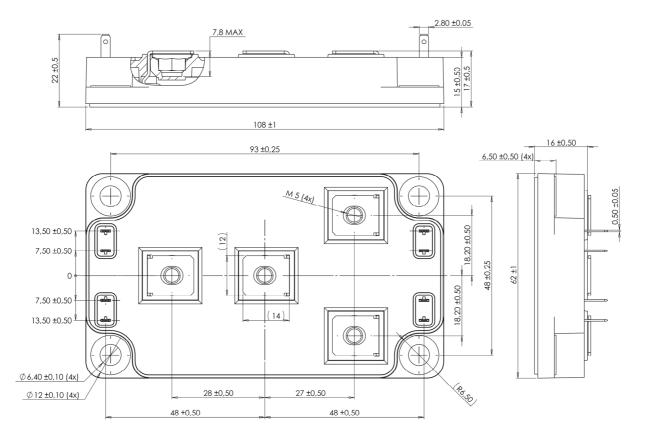
• dv/dt numbers reflect the limitations of the circuit rather than the device itself. $I_S \leq -43A$ $di/dt \le 700 A/\mu s$ $V_R \le V_{DSS}$ $T_j \le 150^{\circ}C$



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance					0.16	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

SP6 Package outline (dimensions in mm)

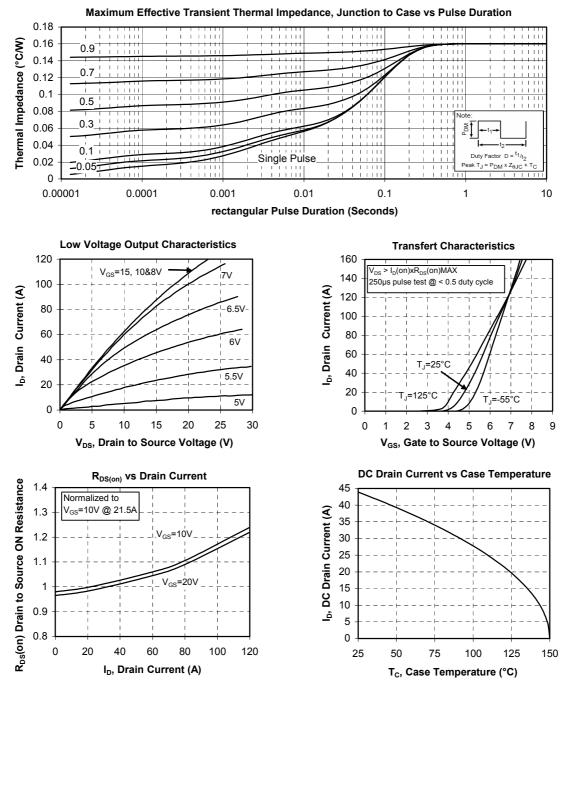


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

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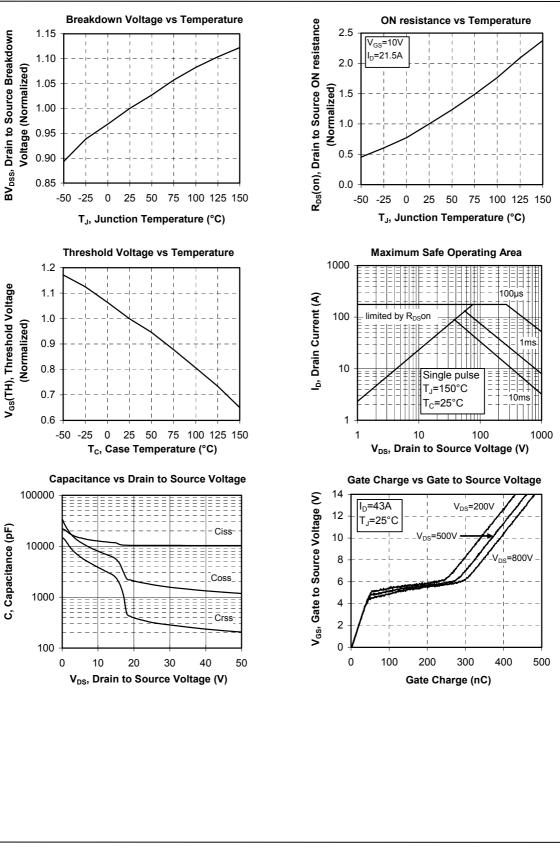
Typical Performance Curve



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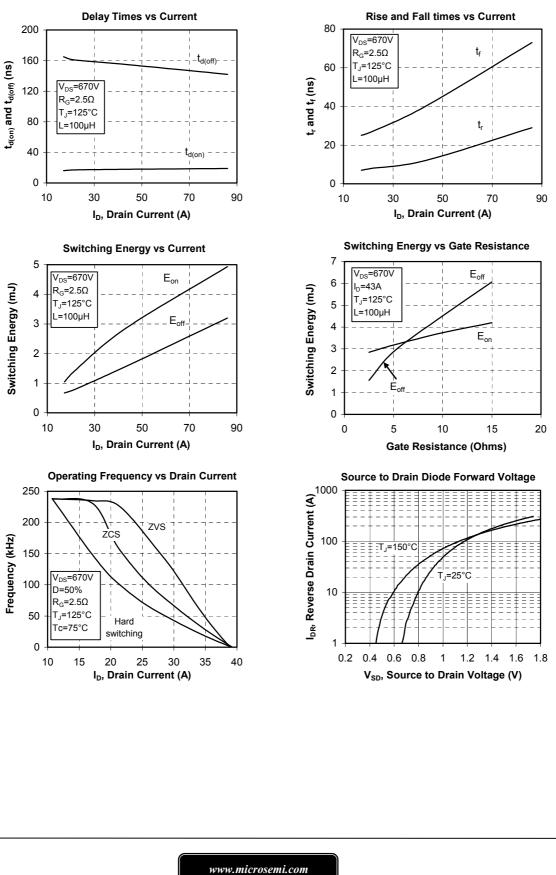




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